2SC2736

Silicon NPN Epitaxial

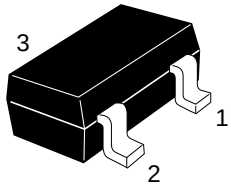
HITACHI

Application

- UHF/VHF frequency converter
- Local oscillator

Outline

MPAK



1. Emitter
2. Base
3. Collector

Hitachi semiconductor

Absolute Maximum Ratings (Ta = 25°C)

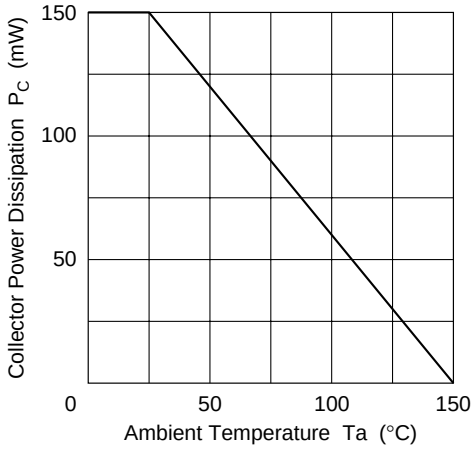
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

Electrical Characteristics (Ta = 25°C)

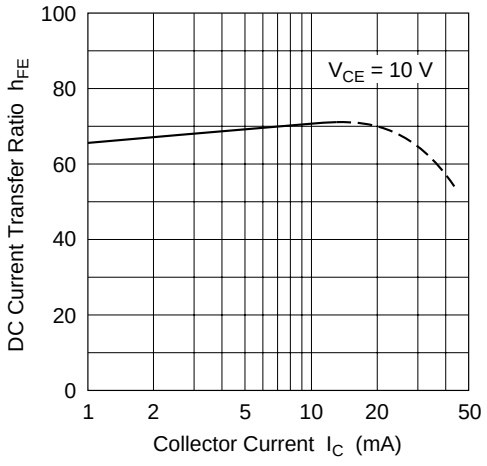
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	V	I_C = 10 µA, I_E = 0
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	—	—	V	I_C = 1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	3	—	—	V	I_E = 10 µA, I_C = 0
Collector cutoff current	I_{CBO}	—	—	500	nA	V_{CB} = 15 V, I_C = 0
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.7	V	I_C = 10 mA, I_B = 5 mA
DC current transfer ratio	h_{FE}	30	—	200		V_{CE} = 10 V, I_C = 5 mA
Collector output capacitance	Cob	—	—	1.0	pF	V_{CB} = 10 V, I_E = 0, f = 1 MHz
Gain bandwidth product	f_T	1400	2200	—	MHz	V_{CE} = 10 V, I_C = 5 mA
Conversion gain	CG_1	—	22.5	—	dB	V_{CC} = 12 V, I_C = 2 mA, f = 200 MHz, f_{OSC} = 230 MHz (0dBm)
	CG_2	—	10	—	dB	V_{CC} = 12 V, I_C = 2 mA, f = 900 MHz, f_{OSC} = 930 MHz (0dBm), f_{Out} = 30 MHz
Noise figure	NF	—	4.0	—	dB	V_{CC} = 12 V, I_C = 2 mA, f = 200 MHz, f_{OSC} = 230 MHz (0dBm)
Oscillating output voltage	V_{OSC1}	—	300	—	mV	V_{CC} = 12 V, I_C = 7 mA, f_{OSC} = 300 MHz
	V_{OSC2}	—	200	—	mV	V_{CC} = 12 V, I_C = 7 mA, f_{OSC} = 930 MHz

Note: Marking is “TC”.

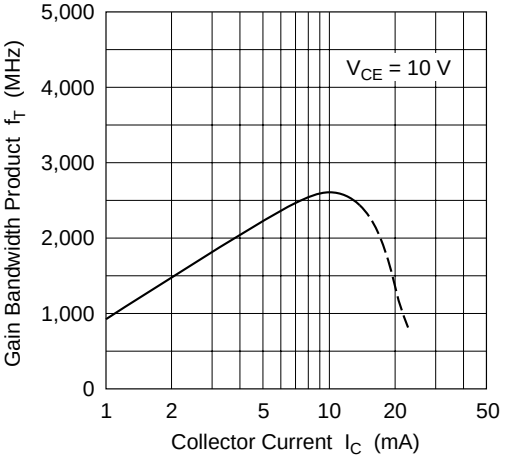
Maximum Collector Dissipation Curve



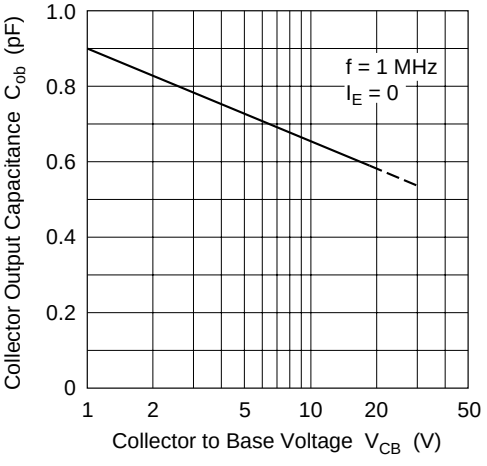
DC Current Transfer Ratio vs. Collector Current



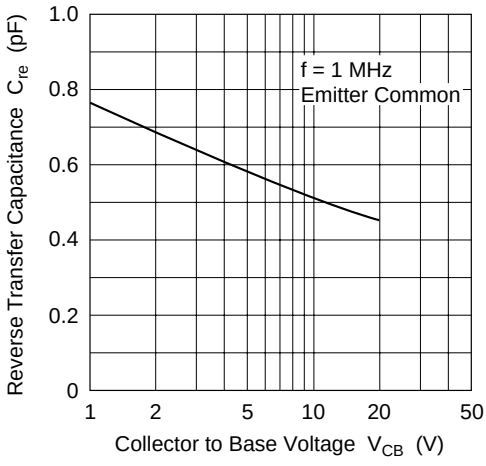
Gain Bandwidth Product vs. Collector Current



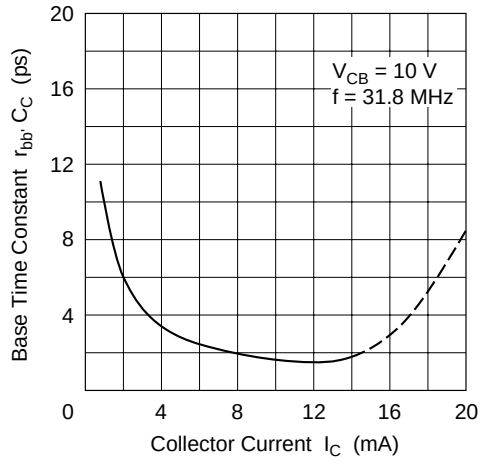
Collector Output Capacitance vs. Collector to Base Voltage



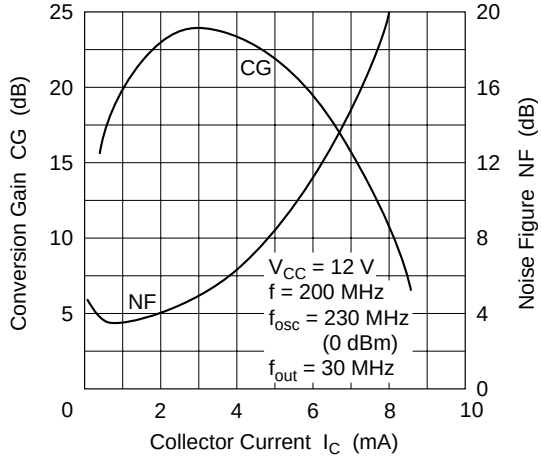
Reverse Transfer Capacitance vs. Collector to Base Voltage



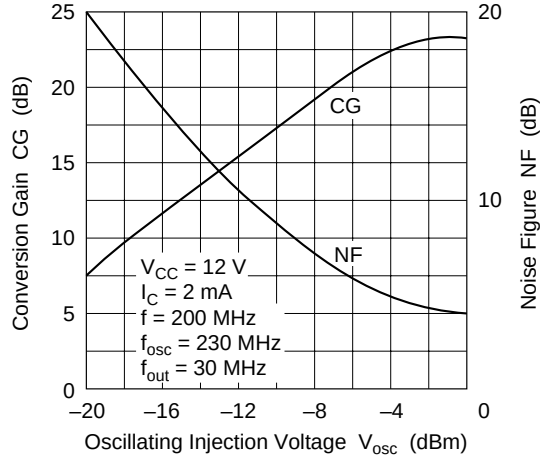
Base Time Constant vs. Collector Current



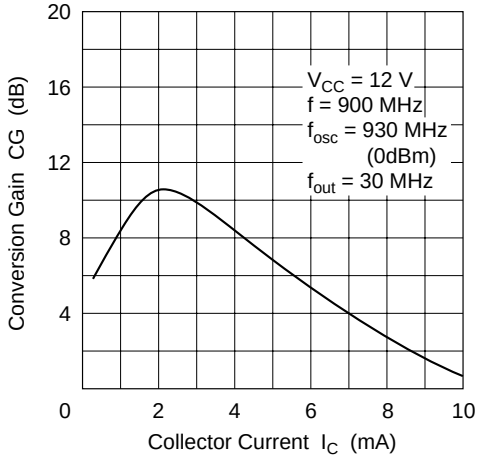
Conversion Gain, Noise Figure vs. Collector Current



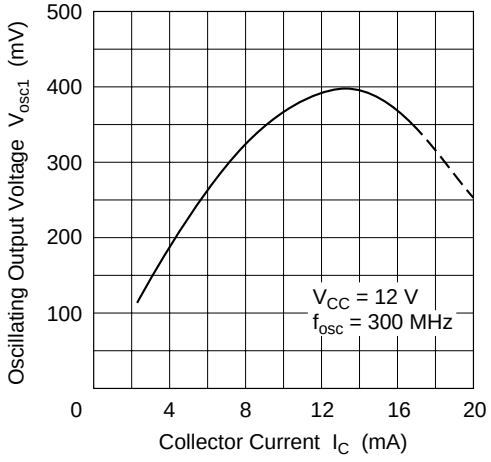
Conversion Gain, Noise Figure vs. Oscillating Injection Voltage



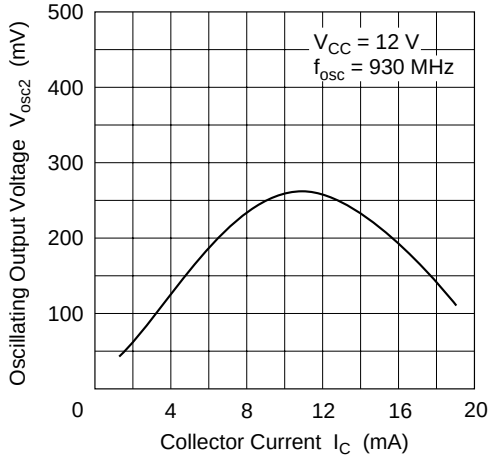
Conversion Gain vs. Collector Current



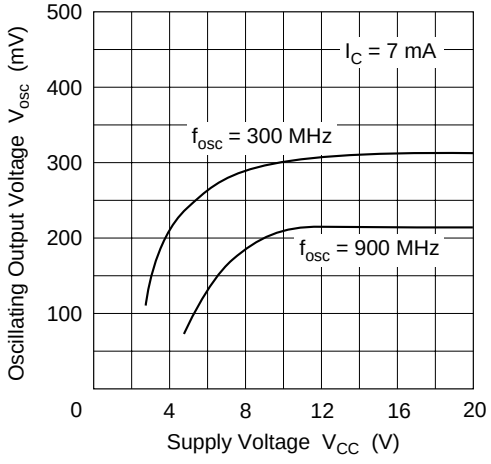
Oscillating Output Voltage vs. Collector Current



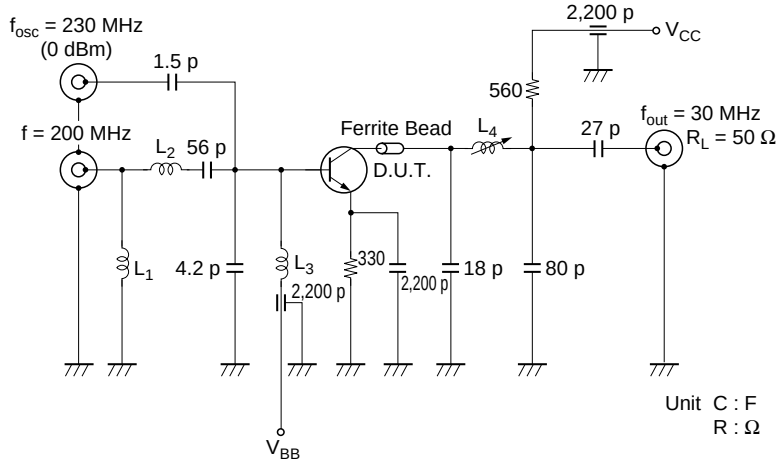
Oscillating Output Voltage vs. Collector Current



Oscillating Output Voltage vs. Supply Voltage



VHF Conversion Gain (CG_1) : Noise Figure Test Circuit



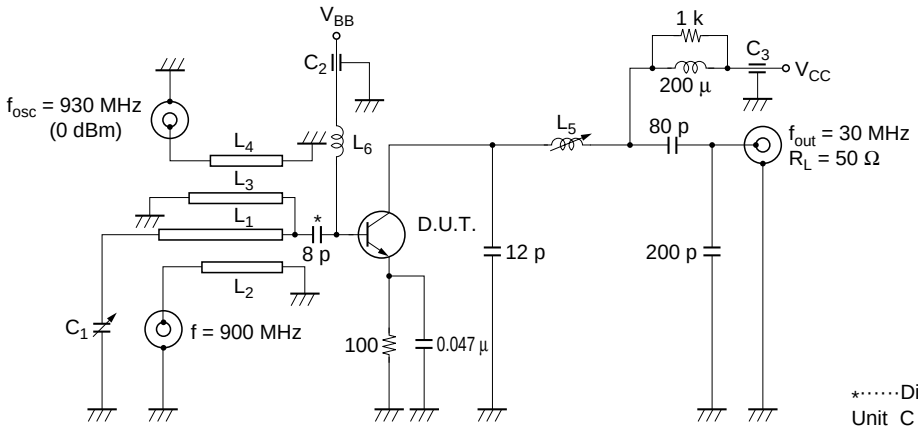
L_1 : ϕ0.5 mm Enameled Copper Wire
4 Turns inside dia ϕ5 mm

L_2 : ϕ0.5 mm Enameled Copper Wire
4 Turns inside dia ϕ4 mm

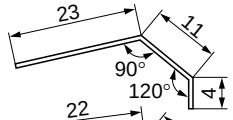
L_3 : ϕ0.2 mm Enameled Copper Wire
6 Turns inside dia ϕ3 mm

L_4 : Outside dia ϕ5 mm Bobbin,
ϕ0.2 mm Enameled Copper Wire
16 Turns Using Ferrite bead.

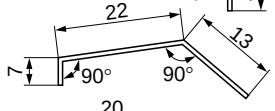
UHF Conversion Gain (CG_2) Test Circuit



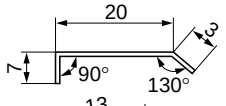
L_1 : ϕ1 mm Enameled Copper Wire



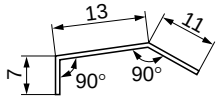
L_2 : ϕ1 mm Enameled Copper Wire



L_3 : ϕ1 mm Enameled Copper Wire



L_4 : ϕ1 mm Enameled Copper Wire



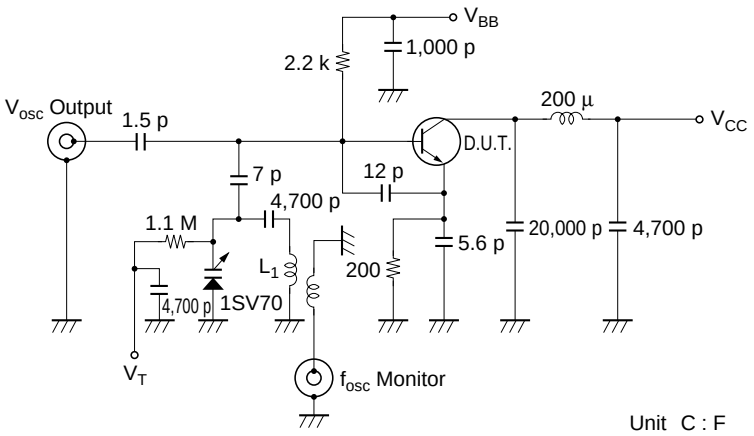
L_5 : Bobbin ϕ5 mm inside dia, ϕ0.2 mm Enameled Copper Wire 20 Turns

L_6 : ϕ0.5 mm Enameled Copper Wire 1 Turn inside dia ϕ6 mm

C_1 : 20 pF max Air Trimmer Condenser

C_2, C_3 : 1000 pF Air Core Capacitor

VHF Oscillating Output Voltage (V_{osc1}) Test Circuit

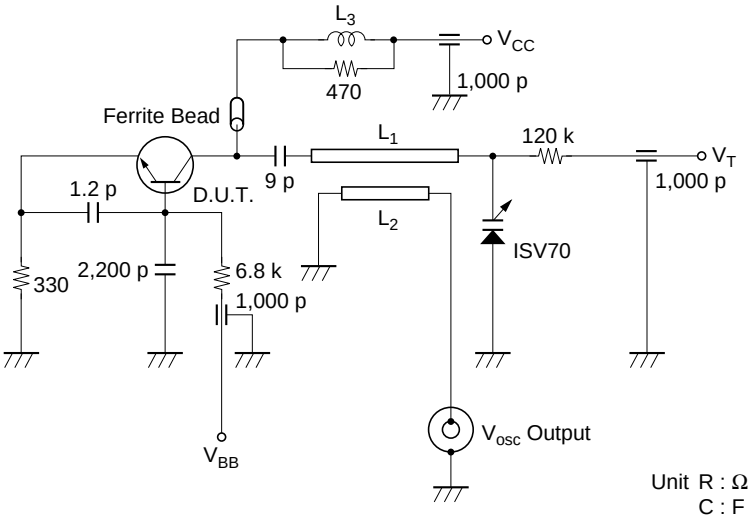


L_1 : ϕ0.3 mm Enameled Copper Wire
3 Turns inside dia ϕ3 mm

Test Frequency
f_{osc} = 300 MHz

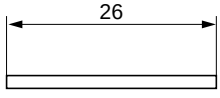
Unit C : F
R : Ω
L : H

UHF Oscillating Output Voltage (V_{osc2}) Test Circuit

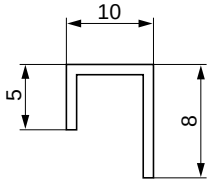


Unit R : Ω
C : F

L_1 : Polyurethane Coated Copper Wire



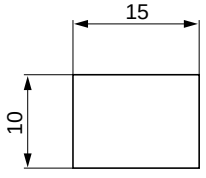
L_2 : Polyurethane Coated Copper Wire



(Unit : mm)

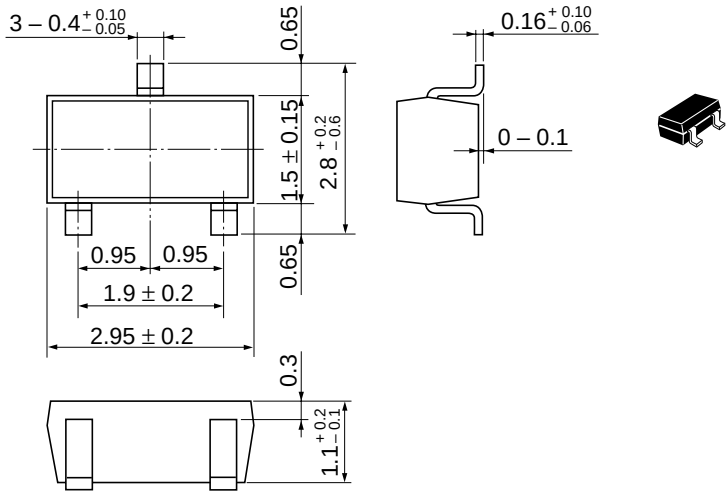
L_3 : ϕ0.3 mm Enameled Copper wire, 10 Turns with 470 Ω (1/4W)Resistor.

Dimensions of Cavity



Test Frequency
f_{osc} = 930 MHz

Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.011 g

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HITACHI

Hitachi, Ltd.
Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building. No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX